<u>.</u>		Search Text	IB	Time stamp
Number		"I.w-k" is dielectric is insulating and resist it phitiresist is pattern or patterning or patterned; and trench or tia or contact or openings, and etch(s)	IBM_TDB	_94:30
3	<u>.</u>	"dual damas vene" (1) dual adj damas vene	USFAT; EEC; 'PC; IBM TLE	
4		"low-k" or dielectric or insulating and (resist of photoresist or pattern or patterning or patterning and french of the incentact or penings and etch23 and ("dual damascene" or dual aid damascene.	usrāt; Ero; Jro; Irmjīds	2003/04 W 1 08:57
<i>c.</i>		<pre>-ash or ashing or ashed and "in-situ" and etch\$3 and "low-k"</pre>	EPO: JPG: IBM TDB	
2		and (resist of photoresist or pattern or patterning or patterned); and (trench or patterning or patterned); and (trench or via or contact or openings) and etch\$3. and ("organo silicate glass" or OSG)	USPĀT; EPO; JPO; IBM_TDB	
ř.		<pre>wash or ashing or ashed same ("water vapor" or "H.sub.20" same (oxygen or "o.sub.0")</pre>	EFD; JFO; IBM TDB	
7	23	reash or ashing or ashed same ("water vapor" or "H.sub.20" same oxygen or "c.sub.2") and ("low-k" or dielectric or insulating; and cresist of photoresist repattern or patterned and (trench or via or contact or openings) and etch\$3	USPAT; EFO; JPC; IBM_TDB	
۵		438009ê.pn.	USPAT; EPN; JPO; IBM_TDB	
ii		dielectric same ""organo silicate glass" or OSG or "black diamond":	USPĀT; EPO; JEC; IBM_TDB	2003 04/01 08:18
14		<pre>dielectric and ("organo silicate glass" or OSG or "black diamond";</pre>	USPAT; EPO; JPO; IBM_TDB	2003#04:01 08:25
15		dielectric and ("organo silicate glass" or OSG $^{\circ}$	USPAT; EPO; JPO; IBM_TDB	2003/04/01
18		"drelectfic constant"and -"organs silicate glass" or OSG	USPĀT; EFO; JEO; IBM_TDB	2003/04/61 09:17 2003/04/61
24		"low-k" or dielectric or insulating and resist of photoresist or pattern of patterning or patterned and tiensh of the contact or openings and etch03 and ash or ashing of ashed	EPI; JFI; IBM_TDB	34:3 <u>0</u>
	4 m 25 m	"""" or dielectric or insulating and cresist of photoresist of pattern of patterning or patterned cland trench rule or contact or openings; and etchto and lash or ashing crashed and 434 \$	EFY/ WFY/ IFM_TDB	
D·	1.42	"low-k" for dielecting or insulating and resist of photograph of patterning or patterned and trench of the contact of openings and etchical and ash or ashing or ashed and 43% Cootles, and "water tapes" of "H.sub.22" and exygen of "Costb.2"	EFT: JF7:	20 / 4 . 29:27